

Vishay Semiconductors

MOSMIC® for TV-Tuner Prestage with 5 V Supply Voltage

Comments

MOSMIC - MOS Monolithic Integrated Circuit

Features

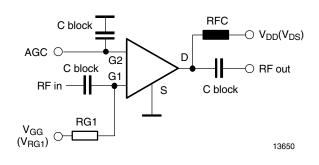
- Easy Gate 1 switch-off with PNP switching transistors inside PLL
- High AGC-range with less steep slope
- Integrated gate protection diodes
- · Low noise figure
- High gain, high forward transadmittance (30 mS typ.)
- · Improved cross modulation at gain reduction
- SMD package
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

SOT-143 SOT-143R SOT-343R SOT-343R Electrostatic sensitive device. Observe precautions for handling.

Applications

Low noise gain controlled input stages in UHF-and VHF- tuner with 5 V supply voltage.

Typical Application



Mechanical Data

Typ: S505TX

Case: SOT-143 Plastic case Weight: approx. 8.0 mg

Pinning: 1 = Source, 2 = Drain,

3 = Gate 2, 4 = Gate 1

Typ: S505TXR

Case: SOT-143R Plastic case

Weight: approx. 8.0 mg

Pinning:1 = Source, 2 = Drain,

3 = Gate 2, 4 = Gate 1

Typ: S505TXRW

Case: SOT-343R Plastic case

Weight: approx. 6.0 mg

Pinning: 1 = Source, 2 = Drain,

3 = Gate 2, 4 = Gate 1

Parts Table

Part	Marking	Package
S505TX	X05	SOT-143
S505TXR	X7R	SOT-143R
S505TXRW	WX7	SOT-343R

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Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Drain - source voltage		V _{DS}	8	V
Drain current		I _D	30	mA
Gate 1/Gate 2 - source peak current		± I _{G1/G2SM}	10	mA
Gate 1 - source voltage		+ V _{G1S}	6	V
		- V _{G1S}	1.5	V
Gate 2 - source voltage		± V _{G2SM}	6	V
Total power dissipation	T _{amb} ≤ 60 °C	P _{tot}	200	mW
Channel temperature		T _{Ch}	150	°C
Storage temperature range		T _{stg}	- 55 to + 150	°C

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit	
Channel ambient	1)	R_{thChA}	450	K/W	

 $^{^{1)}}$ on glass fibre printed board (25 x 20 x 1.5) mm^3 plated with 35 μm Cu

Electrical DC Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Drain - source breakdown voltage	$I_D = 10 \mu A, V_{G1S} = V_{G2S} = 0$	V _{(BR)DSS}	12			V
Gate 1 - source breakdown voltage	$\pm I_{G1S} = 10 \text{ mA}, V_{G2S} = V_{DS} = 0$	± V _{(BR)G1SS}	7		10	V
Gate 2 - source breakdown voltage	$\pm I_{G2S} = 10 \text{ mA}, V_{G1S} = V_{DS} = 0$	± V _{(BR)G2SS}	7		10	V
Gate 1 - source leakage current	$+ V_{G1S} = 5 V, V_{G2S} = V_{DS} = 0$	+ I _{G1SS}			20	nA
Gate 2 - source leakage current	$\pm V_{G2S} = 5 \text{ V}, V_{G1S} = V_{DS} = 0$	± I _{G2SS}			20	nA
Drain - source operating current	$V_{DS} = V_{RG1} = 5 \text{ V}, V_{G2S} = 4 \text{ V},$ $R_{G1} = 56 \text{ k}\Omega$	I _{DSO}	8	14	20	mA
Gate 1 - source cut-off voltage	$V_{DS} = 5 \text{ V}, V_{G2S} = 4, I_{D} = 20 \mu\text{A}$	V _{G1S(OFF)}	0.5		1.3	V
Gate 2 - source cut-off voltage	$V_{DS} = V_{RG1} = 5 \text{ V}, R_{G1} = 56 \text{ k}\Omega,$ $I_D = 20 \mu\text{A}$	V _{G2S(OFF)}	0.8	1.0	1.4	V

Remark on improving intermodulation behavior:

By setting R_{G1} smaller than 56 $k\Omega$, typical value of I_{DSO} will raise and improved intermodulation behavior will be performed.

Electrical AC Characteristics

 T_{amb} = 25 °C, unless otherwise specified

 $V_{DS} = V_{RG1} = 5 \text{ V}, V_{G2S} = 4 \text{ V}, R_{G1} = 56 \text{ k}\Omega, I_D = I_{DSO}, f = 1 \text{ MHz}$

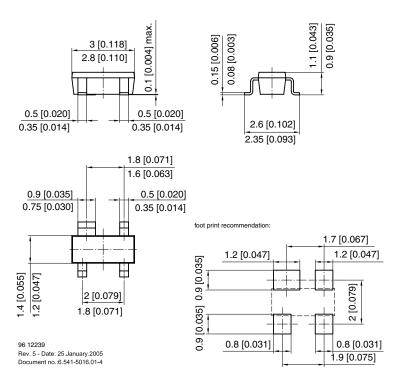
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Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward transadmittance		y _{21s}	27	30	35	mS
Gate 1 input capacitance		C _{issg1}		1.8	2.2	pF
Feedback capacitance		C _{rss}		20	30	fF
Output capacitance		C _{oss}		1.0		pF



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Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Power gain	$G_S = 2 \text{ mS}, G_L = 0.5 \text{ mS},$ f = 200 MHz	G _{ps}		28		dB
	$G_S = 3.3 \text{ mS}, G_L = 1 \text{ mS},$ f = 800 MHz	G _{ps}	17	22		dB
AGC range	$V_{DS} = 5 \text{ V}, V_{G2S} = 1 \text{ to 4 V},$ f = 800 MHz	ΔG_{ps}	45	50		dB
Noise figure	$G_S = 2 \text{ mS}, G_L = 0.5 \text{ mS},$ f = 200 MHz	F		1		dB
	G _S = 3.3 mS, G _L = 1 mS, f = 800 MHz	F		1.3		dB
Cross modulation	Input level for k = 1 % @ 0 dB AGC f_w = 50 MHz, f_{unw} = 60 MHz	X _{mod}	90			dBμV
	Input level for k = 1 % @ 40 dB AGC f_W = 50 MHz, f_{unw} = 60 MHz	X _{mod}	100	105		dBμV

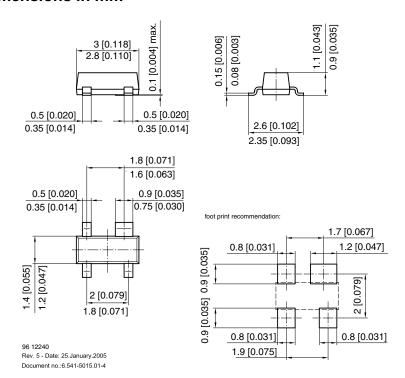
Package Dimensions in mm



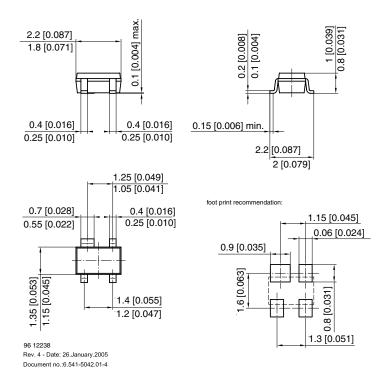
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Package Dimensions in mm





Package Dimensions in mm





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

> We reserve the right to make changes to improve technical design and may do so without further notice.

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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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